

IS1682E

■ Features

1. High speed response (Response frequency : MIN. 55MHz)
(Best suited for optical pick-up in X40 speed CD-ROM drive)
2. With built-in RF amplifier
(Integrates 6-division PIN photodiode and amplifier circuit onto a single chip)
3. Compact and thin package
(Dimensions : 5.0x4.0x1.5mm)
4. Possible to supply custom-made detecting patterns

■ Applications

1. CD-ROM drives (to X40 speed)
2. CD-ROM drives for CD-RW

■ Absolute Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Rating	Unit
Supply voltage	V _{CC}	6.0	V
*1 Output voltage	V _O	V _{CC}	V
Operating temperature	T _{opr}	-30 to +80	°C
Storage temperature	T _{stg}	-40 to +100	°C
*2 Soldering temperature	T _{sol}	260	°C

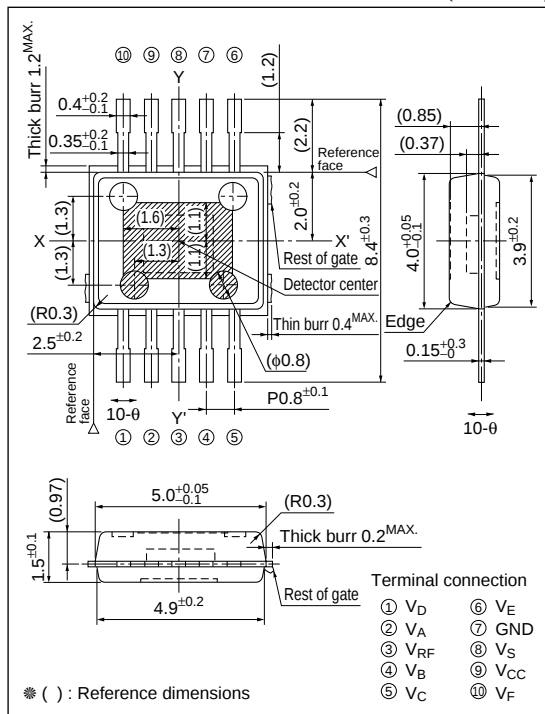
*1 Applies to individual terminals of V_A, V_B, V_C, V_D, V_E, V_F, V_{RF}.

*2 For MAX. 3s at the position of 1.0mm from the resin edge.

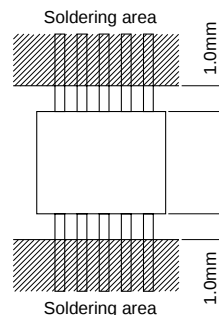
OPIC Light Detector for X40 Speed CD-ROM Drive / CD-RW Drive

■ Outline Dimensions

(Unit : mm)



* "OPIC"(Optical IC) is a trademark of the SHARP Corporation.
An OPIC consists of a light-detecting element and signal-processing circuit integrated onto a signal chip.



■ Recommended Operating Conditions (Ta=25°C)

Parameter	Symbol	MIN	TYP	MAX	Unit
Supply voltage	V _{CC}	4.5	5.0	5.25	V
Recommended supply voltage	V _{CC}	4.75	5.0	5.25	V
Operating supply voltage 1	V _S	2.0	2.1	2.2	V
Operating supply voltage 2	V _S	2.4	2.5	2.6	V

■ Electro-optical Characteristics 1-1 (Ta=25°C, V_{CC}=5V, V_S=2.1V, R_L=10kΩ (V_{RF}: Open), C_L=10pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	Application
Supply current	I _{CC}		8.8	14.8	20	mA	V _{CC}
Output off-set voltage 1	V _{od1}	Specified by voltage difference from V _S	-25	0	+25	mV	V _A to V _D
Output off-set voltage 2	V _{od2}	Specified by voltage difference from V _S	-15	0	+15	mV	V _E , V _F
Output off-set voltage 3	V _{od3}	GND Standard	1.25	1.4	1.55	V	V _{RF}
Extremes of off-set voltage	ΔV _{od}	A-B	-20	0	+20	mV	V _A , V _B
		C-D	-20	0	+20		V _C , V _D
		(A+C)-(B+D)	-20	0	+20		V _A to V _D
		E-F	-15	0	+15		V _E , V _F
		A+B+C+D	-40	+5	+50		V _A to V _D

■ Electro-optical Characteristics 1-2 (Ta=25°C, V_{CC}=5V, V_S=2.5V, R_L=10kΩ (V_{RF}: Open), C_L=10pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	Application
Output off-set voltage 4	V _{od4}	Specified by voltage difference from V _S	-25	+2	+28	mV	V _A to V _D
Output off-set voltage 5	V _{od5}	Specified by voltage difference from V _S	-16	0	+16	mV	V _E , V _F
Output off-set voltage 6	V _{od6}	GND Standard	1.25	1.4	1.55	V	V _{RF}
Extremes of off-set voltage	ΔV _{od}	(A+C)-(B+D)	-22	0	+22	mV	V _A to V _D
		E-F	-15	0	+15		V _E , V _F
		A+B+C+D	-40	+13	+62		V _A to V _D

■ Electro-optical Characteristics 2

(Ta=25°C, VCC=5V, VS=2.1V, RL=10kΩ (V_{RF} : Open), CL=10pF)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	Application
*3*4 Sensitivity 1	R _{p1}	—	18.0	24.6	31.2	mV/μW	V _A to V _D
*3*4 Sensitivity 2	R _{p2}	—	31.2	44.7	58.1	mV/μW	V _E , V _F
*3*4 Sensitivity 3	R _{p3}	—	30.2	43.2	56.1	mV/μW	V _{RF}
*5 Extreme of sensitivity	ΔR _p	—	—	—	10	%	—
Sensitivity ratio 1	R _{p2} /R _{p1}	—	—	1.81	—	—	—
Sensitivity ratio 2	R _{p3} /R _{p1}	—	1.67	1.76	1.84	—	—
*4*6*7 Response frequency 1	f _{c1}	−3dB	50	70	—	MHz	V _A to V _D
*4*6*7 Response frequency 2	f _{c2}	−3dB	55	72	—	MHz	V _{RF}
*4*6*7 Response frequency 3	f _{c3}	−3dB	1	5	—	MHz	V _E , V _F
*4*6*7 Response frequency 4	f _{c4}	Average of V _A to V _D	50	70	—	MHz	V _A to V _D
*4 High level output voltage 1	V _{OH1}	—	3.8	—	—	V	V _A to V _D
*4 High level output voltage 2	V _{OH2}	—	3.8	—	—	V	V _{RF}
*4*7*9 Sensitivity response 1	ΔR _{p1}	1MHz to 23.1MHz	−1.0	+1.0	+2.0	dB	V _A to V _D
*4*7*9 Sensitivity response 2	ΔR _{p2}	1MHz to 23.1MHz	−1.0	+1.0	+2.0	dB	V _{RF}
*4*7*10 Peaking rate 1	ΔR _{p3}	1MHz Standard	—	—	+3.0	dB	V _A to V _D
*4*7*10 Peaking rate 2	ΔR _{p4}	1MHz Standard	—	—	+3.0	dB	V _{RF}
*4*7 Group delay deviation 1	tg _{d1}	f=1 to 23.1MHz, Average of V _A to V _D	—	2.5	5.5	ns	V _A to V _D
*4*7 Group delay deviation 2	tg _{d2}	f=1 to 23.1MHz	—	2.5	5.5	ns	V _{RF}
Output noise level 1	V _{n1}	f=23.1MHz, BW=30kHz	—	−81	−76	dBm	V _A to V _D
Output noise level 2	V _{n2}	f=23.1MHz, BW=30kHz	—	−70	−65	dBm	V _{RF}
Extremes of off-set voltage	ΔV _{od}	A+B+C+D Ta=70°C	−60	+10	+100	mV	V _A to V _D
*8 Difference of output off-set voltage fluctuation temperature characteristics	TCΔV _{od}	(A+B)−(C+D) Ta=25°C to 70°C	−240	−30	+240	μV/°C	V _A to V _D
		E−F, Ta=25°C to 70°C	−150	+50	+150	μV/°C	V _E , V _F
*8 Output off-set voltage fluctuation temperature characteristics	TCV _{od}	GND reference, Ta=25°C to 70°C	—	+5	—	mV/°C	V _{RF}

*3 5μW, φ30μm of DC light is applied to the center of each photodiode.

Under that condition, sensitivity R is shown by following formula.

$$R_p = (V_p - V_{od}) / 5\mu W$$

V_p : Output voltage when DC light is applied.V_{od} : Output voltage when DC light is not applied.

*4 Light source : laser diode of λ=780nm

*5 Extreme of sensitivity is shown by following formula.

$$2 \times (R_{p1\max} - R_{p1\min}) / (R_{p1\max} + R_{p1\min}) \times 100$$

$$2 \times (R_{p2\max} - R_{p2\min}) / (R_{p2\max} + R_{p2\min}) \times 100$$

*6 Frequency sensitivity is −3dB. (reference sensitivity : value at f=1MHz) and f_{c4} is shown by following formula.

$$f_{c4} = (f_{cVA} + f_{cVB} + f_{cVC} + f_{cVD}) / 4$$

*7 In addition to 10μW, φ30μm DC light, 4μWp-p AC light is applied to the center of each photodiode. BW=10kHz

*8 Output off-set voltage deference temperature characteristics and

Output off-set voltage fluctuation temperature characteristics shall be specified by following formula.

$$(\Delta V_{od}(70^\circ C) - \Delta V_{od}(25^\circ C)) / (70 - 25)$$

$$(V_{od}(70^\circ C) - V_{od}(25^\circ C)) / (70 - 25)$$

*9 When VCC is changed from 5V to 4.5V, the increase of sensitivity response is MAX, 0.5Bb.

*10 When VCC is changed from 5V to 4.5V, the increase of peaking rate is MAX, 1Bb.

Fig.1 Detecting Pattern of Photodiode

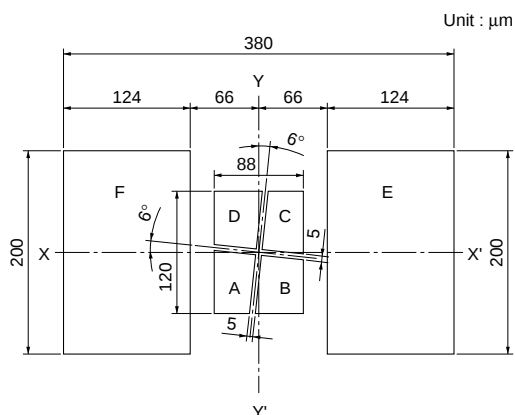


Fig.2 Block Diagram

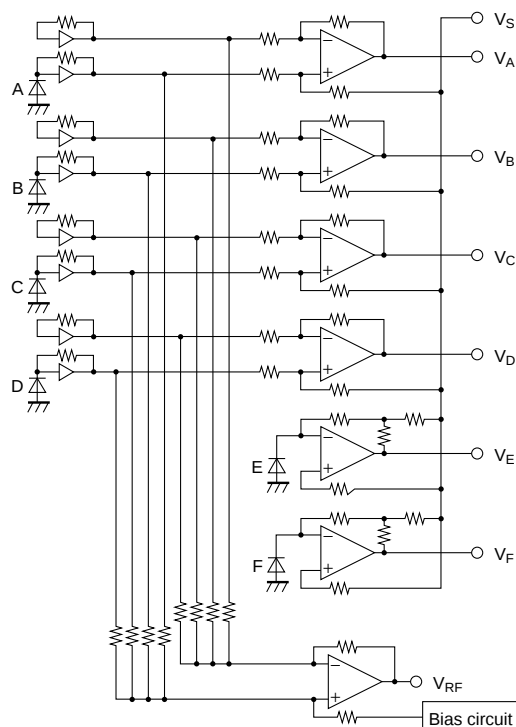


Fig.3 Supply Current vs. Ambient Temperature

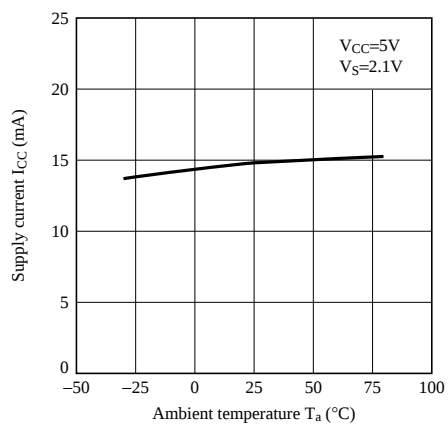
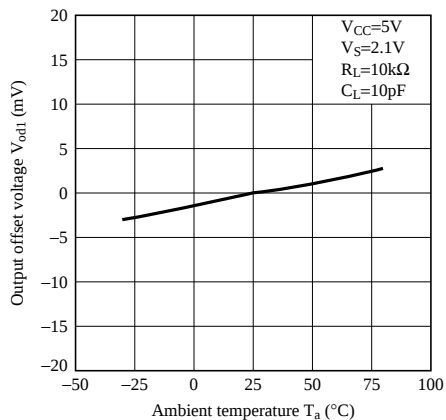
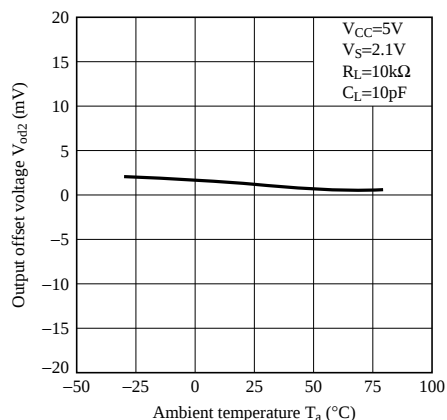
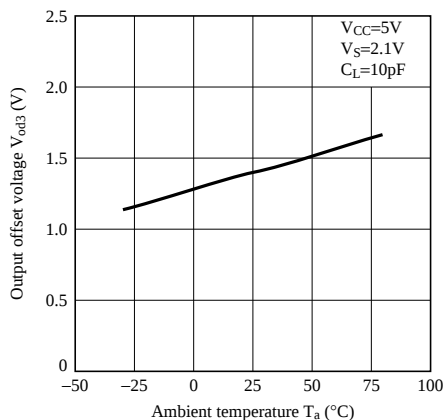
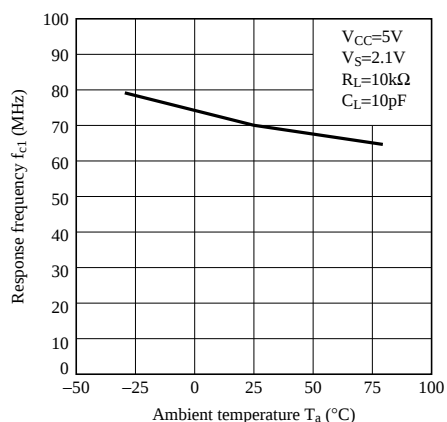
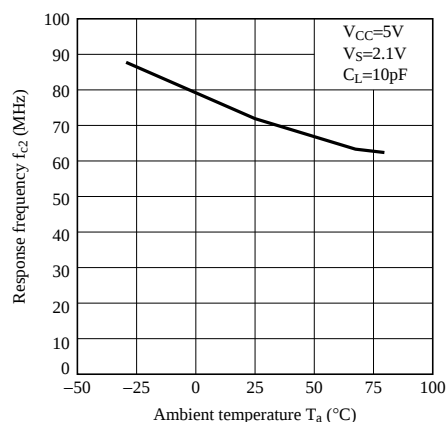
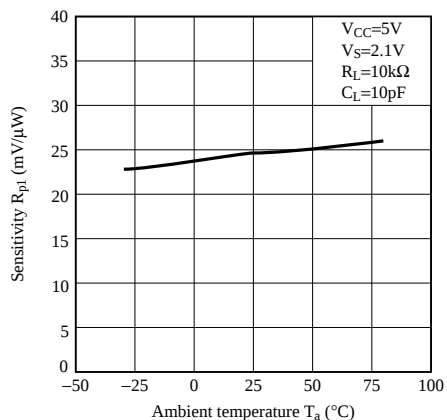
Fig.4 Output Offset Voltage vs. Ambient Temperature (V_A to V_D)

Fig.5 Output Offset Voltage vs. Ambient Temperature (V_E , V_F)**Fig.6 Output Offset Voltage vs. Ambient Temperature (V_{RF})****Fig.7 Response Frequency vs. Ambient Temperature (V_A to V_D)****Fig.8 Response Frequency vs. Ambient Temperature (V_{RF})****Fig.9 Sensitivity vs. Ambient Temperature (V_A to V_D)****Fig.10 Sensitivity vs. Ambient Temperature (V_{RF})**